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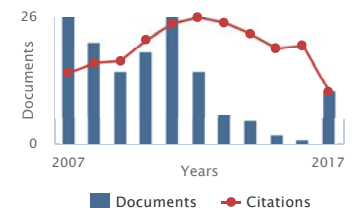
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Author History

Publication range: 1987 - Present

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